1. A method for inspecting semiconductor devices comprising the steps of:

setting inspection conditions using semiconductor device design data;

inspecting semiconductor devices with these set conditions:

using results of this inspection to revise set
inspection conditions with said design data; and
inspecting semiconductor devices using these revised
inspection conditions.

- 2. The method for inspecting semiconductor devices according to claim 1, wherein information that states whether or not an area for inspection is in an area in which false alarms tend to occur is added to inspection conditions set using said design data.
- 3. The method for inspecting semiconductor devices according to claim 1, wherein inspection conditions set using said design data are revised so that only actual foreign matter is detected based on results of a review and classification of defects detected during inspection of said semiconductor devices and so that the percentage of false alarms is less than or equal to a certain amount.

comprising the steps of:

specifying a semiconductor device product name and names of processes used to process this product and extracting related information from a design data base;

setting inspection conditions using this extracted related information;

inspecting semiconductor devices with these set conditions;

using results of this inspection to revise set inspection conditions using said design data;

inspecting semiconductor devices using these revised inspection conditions; and

outputting results of this inspection.

- 5. The method for inspecting semiconductor devices according to claim 4, wherein information that states whether or not an area for inspection is in an area in which false alarms tend to occur is added to inspection conditions set using said design data.
- 6. The method for inspecting semiconductor devices according to claim 4, wherein inspection conditions set using said design data are revised so that only actual foreign matter is detected based on results of a review and classification of defects detected during inspection of said semiconductor devices and so that the percentage of false alarms is less than or equal to a certain amount.

7. A method for inspecting semiconductor devices comprising the steps of:

setting semiconductor device inspection conditions;

detecting defects by inspecting semiconductor

devices using these set conditions;

classifying these detected defects;

revising said set inspection conditions using these classification results; and

inspecting semiconductor devices using these revised inspection conditions.

- 8. The method for inspecting semiconductor devices according to claim 7, wherein images of said classified defects are displayed on a screen.
- 9. The method for inspecting semiconductor devices according to claim 7, wherein, in said step of revising said inspection conditions, said classified defects are reviewed, and said set inspection conditions are revised using results of this review.
- 10. The method for inspecting semiconductor devices according to claim 7, wherein, in said step of setting said inspection conditions, said semiconductor device design data is used.